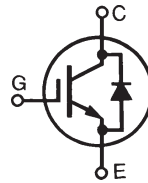


HiPerFAST™ IGBT with Diode ISOPLUS247™

(Electrically Isolated Backside)

IXGR 32N60CD1

$V_{CES} = 600 \text{ V}$
 $I_{C25} = 45 \text{ A}$
 $V_{CE(SAT)} = 2.7 \text{ V}$
 $t_{fi(typ)} = 55 \text{ ns}$

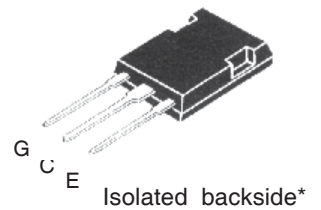


Preliminary data sheet

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	600	V
V_{CGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GE} = 1 \text{ M}\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	45	A
I_{C90}	$T_C = 90^\circ\text{C}$	28	A
I_{CM}	$T_C = 25^\circ\text{C}, 1 \text{ ms}$	120	A
SSOA (RBSOA)	$V_{GE} = 15 \text{ V}, T_{VJ} = 125^\circ\text{C}, R_G = 10 \Omega$ Clamped inductive load, $L = 100 \mu\text{H}$	$I_{CM} = 64$ @ $0.8 V_{CES}$	A
P_c	$T_C = 25^\circ\text{C}$	140	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
Maximum Lead and Tab temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
V_{ISOL}	50/60 Hz, RMS $t = 1 \text{ min leads-to housing}$	2500	V~
Weight		5	g

ISOPLUS247™ (IXGR)

 E 153432



G = Gate, C = Collector,
E = Emitter, TAB = Collector

* Patent pending

Features

- DCB Isolated mounting tab
- Meets TO-247AD package Outline
- High current handling capability
- Latest generation HDMOS™ process
- MOS Gate turn-on - drive simplicity

Applications

- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies
- AC motor speed control
- DC servo and robot drives
- DC choppers

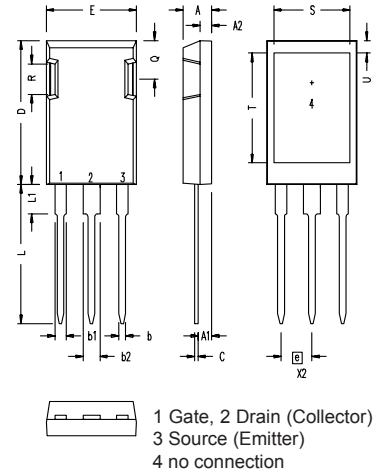
Advantages

- Easy assembly
- High power density
- Very fast switching speeds for high frequency applications

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
$V_{GE(th)}$	$I_C = 250 \mu\text{A}, V_{CE} = V_{GE}$	2.5		5.0 V
I_{CES}	$V_{CE} = 600\text{V}$ $V_{GE} = 0 \text{ V}$			200 μA 3 mA
I_{GES}	$V_{CE} = 0 \text{ V}, V_{GE} = \pm 20 \text{ V}$			$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = I_T, V_{GE} = 15 \text{ V}$ Note 1	2.3	2.7	V

Symbol	Test Conditions	Characteristic Values		
		(T _J = 25°C, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	I _C = I _T ; V _{CE} = 10 V, Pulse test, t ≤ 300 μs, duty cycle ≤ 2 %		25	S
C_{ies}	V _{CE} = 25 V, V _{GE} = 0 V, f = 1 MHz		2700	pF
C_{oes}			240	pF
C_{res}			50	pF
Q_g	I _C = I _T , V _{GE} = 15 V, V _{CE} = 0.5 V _{CES}		110	nC
Q_{ge}			22	nC
Q_{gc}			40	nC
t_{d(on)}	Inductive load, T_J = 25°C I _C = I _T , V _{GE} = 15 V, L = 100 μH, V _{CE} = 0.8 V _{CES} , R _G = R _{off} = 4.7 Ω Remarks: Switching times may increase for V _{CE} (Clamp) > 0.8 • V _{CES} , higher T _J or increased R _G		25	ns
t_{ri}			20	ns
t_{d(off)}			85	170 ns
t_{fi}			55	ns
E_{off}			0.32	0.75 mJ
t_{d(on)}	Inductive load, T_J = 125°C I _C = I _T , V _{GE} = 15 V, L = 100 μH V _{CE} = 0.8 V _{CES} , R _G = R _{off} = 4.7 Ω Remarks: Switching times may increase for V _{CE} (Clamp) > 0.8 • V _{CES} , higher T _J or increased R _G		25	ns
t_{ri}			25	ns
E_{on}			1	mJ
t_{d(off)}			110	ns
t_{fi}			100	ns
E_{off}			0.85	mJ
R_{thJC}				0.90 K/W
R_{thCK}			0.15	K/W

ISOPLUS 247 OUTLINE



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A ₁	2.29	2.54	.090	.100
A ₂	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b ₁	1.91	2.13	.075	.084
b ₂	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	.244
R	4.32	4.83	.170	.190

Symbol	Test Conditions	Characteristic Values		
		(T _J = 25°C, unless otherwise specified)		
		min.	typ.	max.
V_F	I _F = I _T , V _{GE} = 0 V, Pulse test t ≤ 300 μs, duty cycle d ≤ 2 %	T _J = 150°C T _J = 25°C		1.6 V 2.5 V
I_{RM}	I _F = I _T , V _{GE} = 0 V, -di _F /dt = 100 A/μs V _R = 100 V I _F = 1 A; -di _F /dt = 100 A/μs; V _R = 30 V		6	A
t_{rr}		T _J = 100°C	100	ns
t_{rr}		T _J = 25°C	25	ns
R_{thJC}				1.15 K/W

Note: 1. I_T = 32A

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	

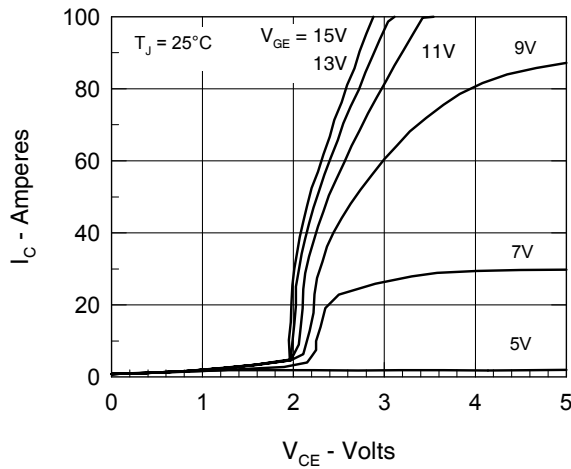


Fig. 1. Output Characteristics

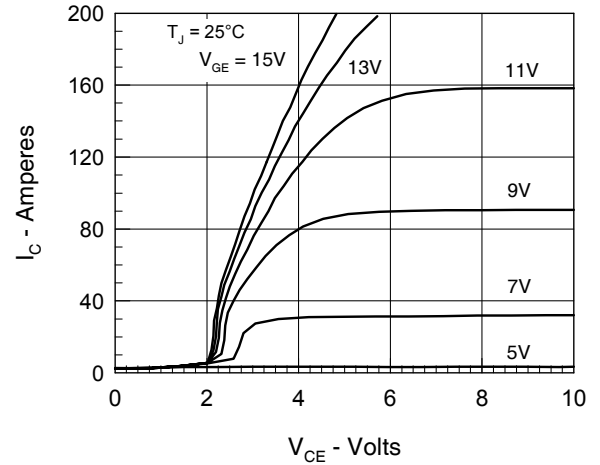


Fig. 2. Extended Output Characteristics

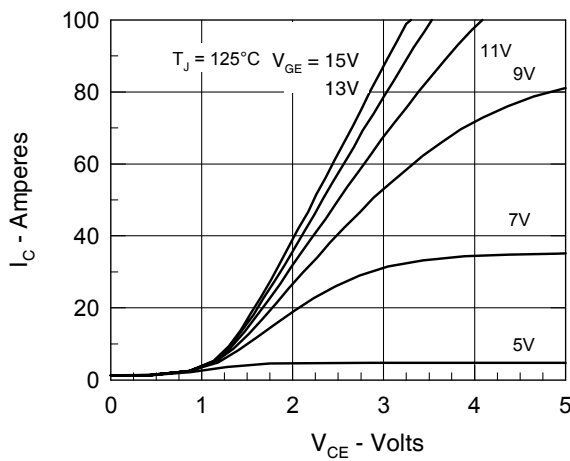


Fig. 3. High Temperature Output Characteristics

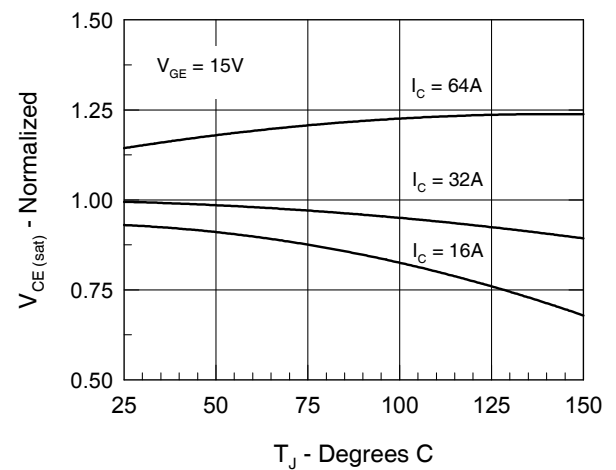
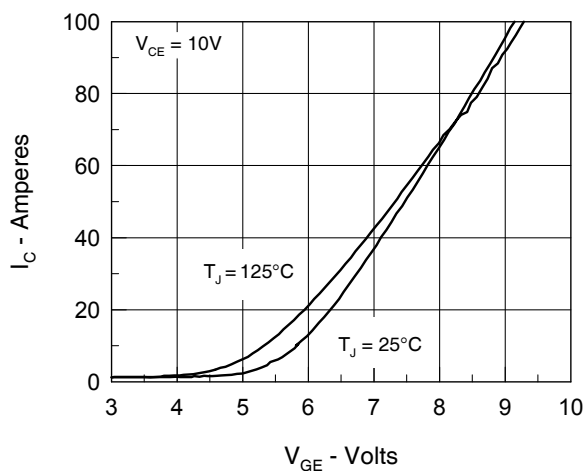

 Fig. 4. Temperature Dependence of $V_{CE(sat)}$


Fig. 5. Admittance Curves

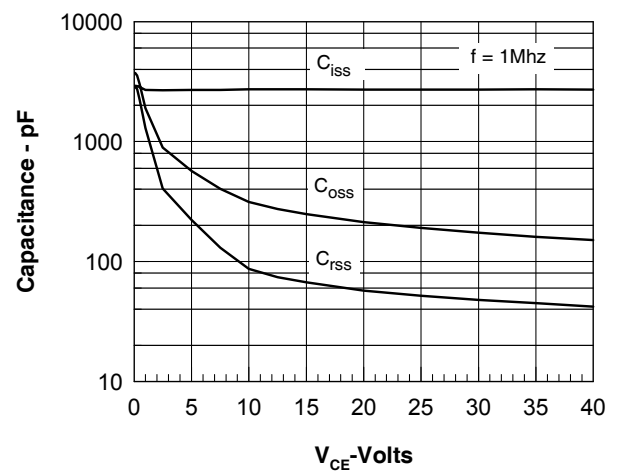


Fig. 6. Capacitance Curves

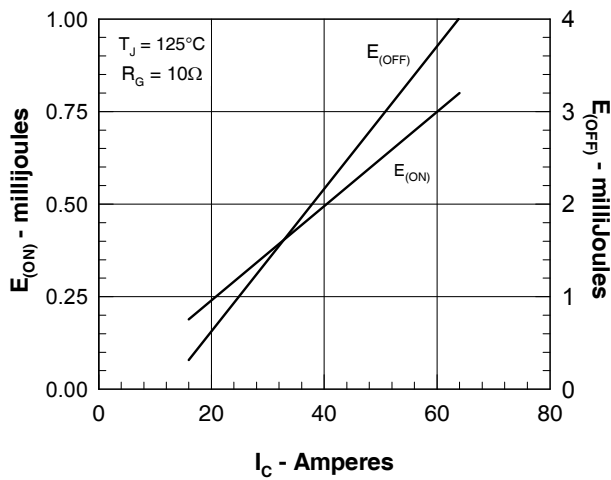


Fig. 7. Dependence of E_{ON} and E_{OFF} on I_C .

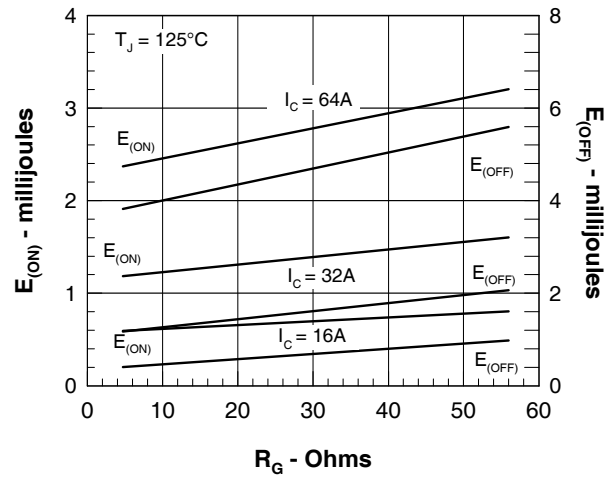


Fig. 8. Dependence of E_{ON} and E_{OFF} on R_G .

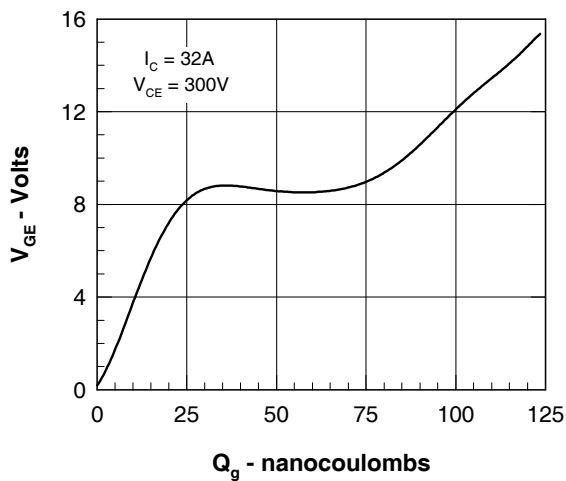


Fig. 9. Gate Charge

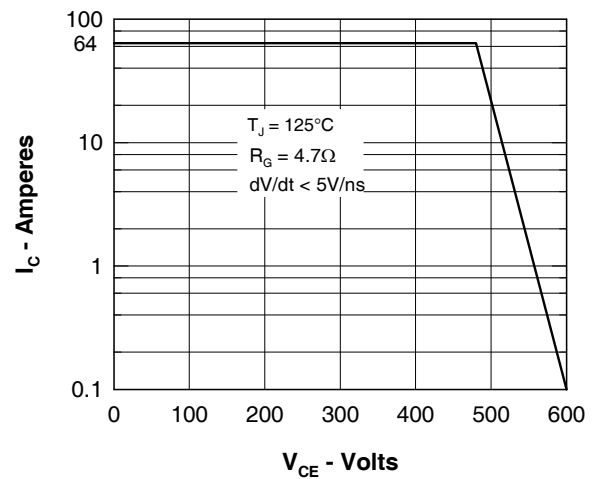


Fig. 10. Turn-off Safe Operating Area

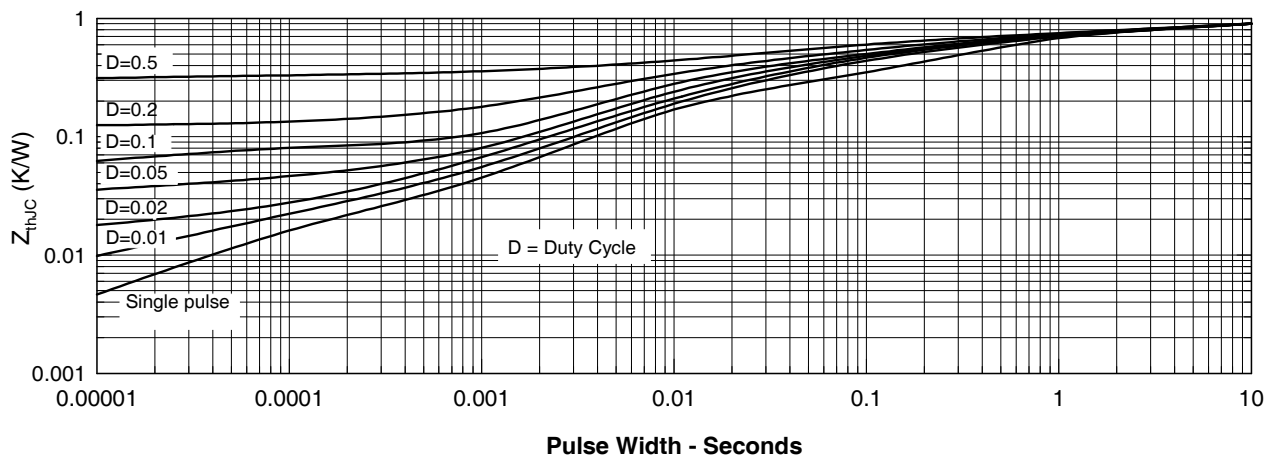


Fig. 11. Transient Thermal Resistance

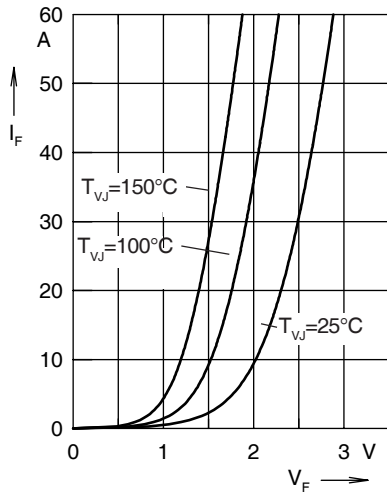


Fig. 12. Forward current I_F versus V_F

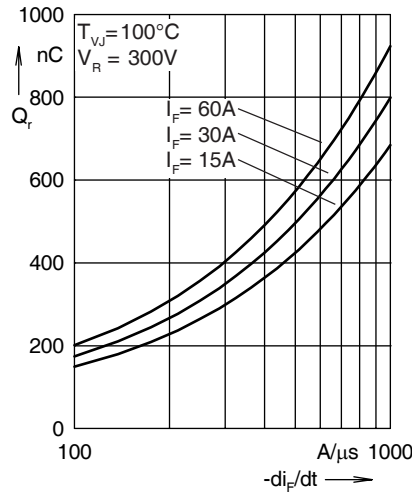


Fig. 13. Reverse recovery charge Q_r versus $-di_F/dt$

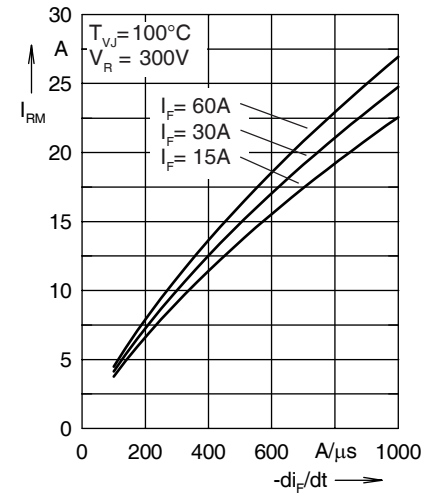


Fig. 14. Peak reverse current I_{RM} versus $-di_F/dt$

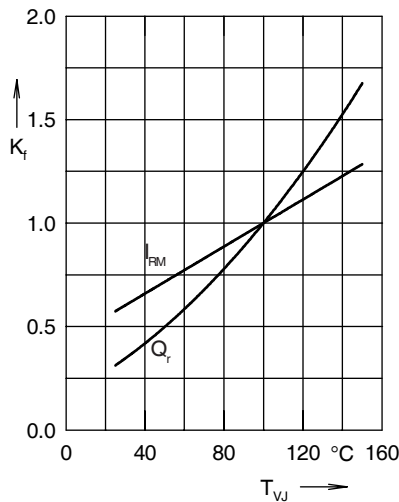


Fig. 15. Dynamic parameters Q_r , I_{RM} versus T_{VJ}

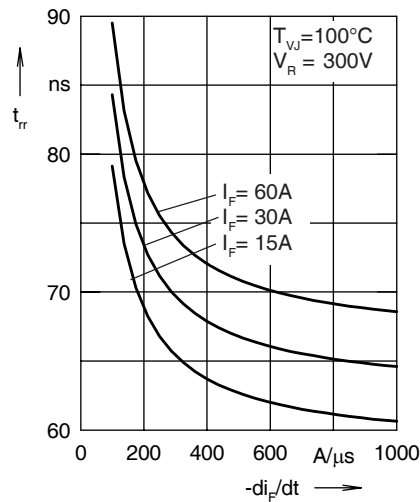


Fig. 16. Recovery time t_{rr} versus $-di_F/dt$

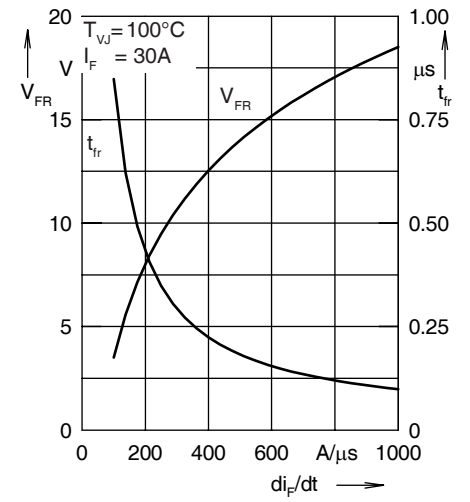


Fig. 17. Peak forward voltage V_{FR} and t_{fr} versus di_F/dt

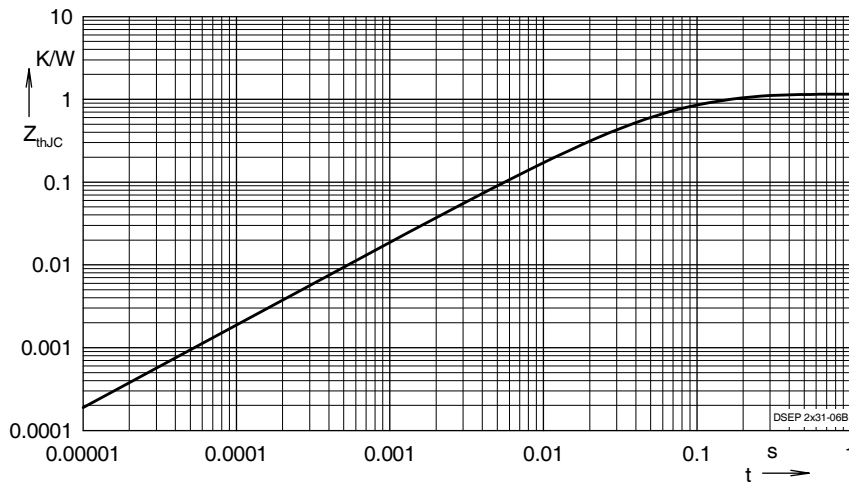


Fig. 18. Transient thermal resistance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.436	0.0055
2	0.482	0.0092
3	0.117	0.0007
4	0.115	0.0418